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 GIORGI et al.

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE (IF APPROPRIATE)
LSD		3,590,344	06/29/71	Roberts et al.	257	116	
		4,186,409	01/29/80	McMullin	257	117	
		4,219,833	08/26/80	Temple	257	115	
		4,497,109	02/05/85	Huber et al.	257	113	
		4,572,947	02/28/86	Kao et al.	257	118	
		4,866,500	09/12/89	Nishizawa et al.	257	114	
		4,908,687	03/13/90	Temple	257	115	
		5,017,991	05/21/91	Nishizawa et al.	257	114	
		5,747,835	05/05/98	Pezzani	257	113	
		6,218,682	04/17/01	Zucker et al.			

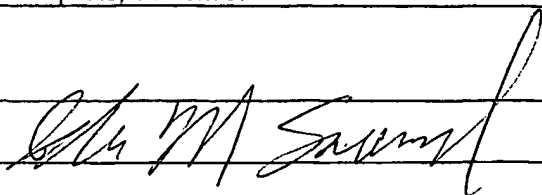
FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
LSD		DE 002738160	03/01/79	Germany			Abstract	
		JP 353112682	10/02/78	Japan			Abstract	
		JP 356152266	11/25/81	Japan			Abstract	
		JP 357196567	12/02/82	Japan			Abstract	
		JP 407015004A	01/17/95	Japan			Abstract	

OTHER DOCUMENTS

LSD		Alferov et al., "Electrically controllable three-electrode high-voltage subnanosecond switches made from a multilayer GaAs-AlGaAs heterostructure", <u>Sov. Tech Phys Lett.</u> November, 1986, American Institute of Physics, pp. 529-530.
		Carson et al., "Long switching delay mechanisms for optically triggered GaAs thyristors", <u>Appl. Phys. Lett.</u> August 1991, American Institute of Physics, pp. 834-836.
		Long et al., "New experiments with Light Activated Silicon Switches", <u>Appl. Phys. Lett.</u> December 27, 1977, pp. 1-3.
		Page, "Some Advances in High Power, High di/dt, Semiconductor Switches", <u>Energy Storage, Compression and Switching</u> , 1976, pp. 415-421.
		Zhao et al., "Dynamic I-V Characteristics of an AlGaAs/GaAs-Based Optothyristor for Pulsed Power-Switching Applications", <u>IEEE Electronic Device Letters</u> , Vol. 13, No. 3, March 1992, pp. 161-163.
		Zhao et al., "Using Reverse Dynamic I-V Characteristics of AlGaAs/GaAs Optothyristor for Pulsed Power-Switching Applications", <u>Electronics Letters</u> , May 21, 1992, Vol. 28, No. 11, pp. 977-978.
		Zucker et al., "Experimental demonstration of high-power fast-rise-time switching in silicon junction semiconductors", <u>Applied Physics Letters</u> , Vol. 29, No. 4, August 15, 1976, pp. 261-263.
MD		"Proceedings: Light-Fired Thyristor Workshop", March 1978, Electric Power Research Institute, Palo Alto, California.

Examiner:



Date Considered:

